IN THE CLAIMS:

Claim1. (currently amended): A semiconductor light emitting device comprising:

an active layer composed of a nitride based semiconductor;

a cladding layer formed on said active layer, composed of a nitride based semiconductor of a first conductivity type, and having a flat portion and a ridge portion formed on the flat portion; ~~and~~

a first current blocking layer formed on said flat portion and on sidewalls of said ridge portion of said cladding layer and composed of a high-resistive nitride based semiconductor containing impurities; and

a second current blocking layer formed on said first current blocking layer and composed of a nitride based semiconductor of a second conductivity type opposite to said first conductivity type;

wherein the cladding layer is composed of AlGaN; ~~and~~

wherein the first current blocking layer is composed of AlGaN having a larger Al composition ratio than that of the cladding layer; and

wherein said impurities contain at least one of zinc, beryllium, calcium, and carbon.

a second current blocking layer formed on said first current blocking layer and composed of a nitride based semiconductor of a second conductivity type opposite to said first conductivity type;

wherein the cladding layer is composed of AlGaN;

wherein the first current blocking layer is composed of AlGaN having a larger Al composition ratio than that of the cladding layer; and

wherein said impurities contain at least one of zinc, beryllium, calcium, and carbon.

Claim 2 (cancelled)

Claim 3 (original): The semiconductor light emitting device according to claim 1, wherein said first current blocking layer has a resistance value of not less than 1.5 Ω·cm

Claim 4 (cancelled)

Claim 5 (original): The semiconductor light emitting device according to claim 1, wherein the thickness of said first current blocking layer is not less than 0.5 μm.

Claim 6 (original): The semiconductor light emitting device according to claim 5, wherein the thickness of said first current blocking layer is not less than 1.0 μm.

Claim 7 (original): The semiconductor light emitting device according to claim 1, wherein the thickness of the flat portion of said cladding layer is not more than 0.3 μm.

Claim 8 (original): The semiconductor light emitting device according to claim 7, whereinthe thickness of the flat portion of said cladding layer is not more than 0.08 μm.

Claim 9 (original): The semiconductor light emitting device according to claim 1, wherein said nitride based semiconductor contains at least one of boron, gallium, aluminum, indium, and thallium.

Claim 10 (currently amended): A semiconductor light emitting device comprising:

an active layer composed of a nitride based semiconductor;

a cladding layer formed on said active layer, composed of a nitride based semiconductor of a first conductivity type, and having a flat portion and a ridge portion formed on the flat portion; ~~and~~

a first current blocking layer formed on said flat portion and on sidewalls of said ridge portion of said cladding layer and composed of a high-resistive nitride based semiconductor containing impurities; and

a second current blocking layer formed on said first current blocking layer and composed of a nitride based semiconductor of a second conductivity type opposite to said first conductivity type;

wherein the cladding layer is composed of AlGaN; ~~and~~

wherein the first current blocking layer is composed of AlGaN having a larger Al composition ratio than that of the cladding layer;

wherein said first current blocking layer is composed of a high-resistive nitride based semiconductor containing impurities; and

wherein said impurities contain at least one of zinc, beryllium, calcium, and carbon.

Claim 11 (cancelled)

Claim 12 (cancelled)

Claim 13 (original): The semiconductor light emitting device according to claim 10, wherein said first current blocking layer has a resistance value of not less than 1.5 Ω·cm.

Claim 14 (cancelled):

Claim 15 (original): The semiconductor light emitting device according to claim 10, wherein the thickness of said first current blocking layer is not less than 0.5 μm.

Claim 16 (original): The semiconductor light emitting device according to claim 15, wherein the thickness of said first current blocking layer is not less than 1.0 μm.

Claim 17 (original): The semiconductor light emitting device according to claim 10, wherein the thickness of the flat portion of said cladding layer is not more than 0.3 μm.

Claim 18 (original): The semiconductor light emitting device according to claim 17, wherein the thickness of the flat portion of said cladding layer is not more than 0.08 μm.

Claim 19 (original): The semiconductor light emitting device according to claim 10, said nitride based semiconductor contains at least one of boron, gallium, aluminum, indium, and thallium.